

a first dense defect layer provided between the first electrode and the layers of the hetero-configuration, the first dense defect layer being made of a material having a concentration of crystal defects, a value of a lattice constant, and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration.

6. (Twice Amended) A semiconductor light emitting device comprising:

a hetero-configuration having an active layer that emits light when charge carriers are injected, a first clad layer, and a second clad layer, the active layer being interposed between the clad layers, the first and second clad layers [keeping] each having an approximately equal layer thickness acting to keep the injected charge carriers in the active layer;

a first and a second electrode, the layers of the hetero-configuration being interposed between the electrodes;

a dense defect layer provided between the first electrode and the layers of the hetero-configuration, the dense defect layer being made of a material having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration;

a current diffusion layer provided between the first electrode and the dense defect layer, the current diffusion layer diffusing current applied through the first electrode;

a contact layer provided between the first electrode and the current diffusion layer, the contact layer making ohmic contact between the first electrode and the current diffusion layer;

a semiconductor substrate provided between the second electrode and the layers of the

hetero-configuration;

a buffer layer provided on the semiconductor substrate, the buffer layer helping to impede remotely generated crystal defects from reaching the active layer; and

a reflective layer provided on the buffer layer, the reflective layer reflecting light emitted by the active layer so that the emitted light does not enter the buffer layer and the semiconductor substrate.

7. (Twice Amended) A semiconductor light emitting device comprising:

a hetero-configuration having an active layer that emits light when charge carriers are injected, a first clad layer and a second clad layer, the active layer being interposed between the clad layers, the first and second clad layers [keeping] each having an approximately equal layer thickness acting to keep the injected charge carriers in the active layer;

a first and a second electrode, the layers of the hetero-configuration being interposed between the electrodes;

a first dense defect layer provided between the first electrode and the layers of the hetero-configuration, the first dense defect layer being made of a material having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration;

a current diffusion layer provided between the first electrode and the first dense defect layer, the current diffusion layer diffusing current applied through the first electrode;

a contact layer provided between the first electrode and the current diffusion layer, the contact layer making ohmic contact between the first electrode and the current diffusion layer;

a second dense defect layer provided between the second electrode and the layers of the hetero-configuration, the second dense defect layer being made of a material having a concentration of crystal defects, a value of a lattice constant and a thickness which together prevent at least some of the crystal defects generated remotely from the layers of the hetero-configuration from reaching the layers of the hetero-configuration; and

a buffer layer provided on the second electrode, the buffer layer helping to impede remotely generated crystal defects from reaching the active layer.

8. (Amended) The device according to Claim 1, wherein the concentration of crystal defects is $10^4/\text{cm}^2$ or greater[, the value of the lattice constant is 10^{-2} or greater,] and the thickness of the first dense defect layer is 10nm or greater.

9. (Amended) The device according to Claim 6, wherein the minimum concentration of crystal defects is $10^4/\text{cm}^2$ or greater[, the value of the lattice constant is 10^{-2} or greater,] and the thickness of the [first] dense defect layer is 10nm or greater.

10. (Amended) The device according to Claim 7, wherein both of the minimum concentrations of crystal defects are $10^4/\text{cm}^2$ or greater[, both of the minimum values of lattice constants are 10^{-2} or greater,]and the thickness of the first and the second dense defect layers is 10nm or greater.

REMARKS

Favorable reconsideration of this application, as amended, is respectfully requested.

Claims 1-10 are now present in this application. Claims 1 and 6-10 have been amended to clarify and better highlight the present invention without the introduction of any new matter.